

Infrarot-LED mit hoher Ausgangsleistung
High Power Infrared LED
Lead (Pb) Free Product - RoHS Compliant

SFH 4258
SFH 4259



Wesentliche Merkmale

- Infrarot LED mit hoher Ausgangsleistung
- Emissionswellenlänge typ. 850nm
- Halbwinkel SFH 4258: $\pm 15^\circ$
- Halbwinkel SFH 4259: $\pm 25^\circ$
- Hohe Bestromung bei hohen Temperaturen möglich

Anwendungen

- Infrarotbeleuchtung für CMOS Kameras
- IR-Datenübertragung
- Sensorik

Sicherheitshinweise

Je nach Betriebsart emittieren diese Bauteile hochkonzentrierte, nicht sichtbare Infrarot-Strahlung, die gefährlich für das menschliche Auge sein kann. Produkte, die diese Bauteile enthalten, müssen gemäß den Sicherheitsrichtlinien der IEC-Norm 60825-1 behandelt werden.

Features

- High Power Infrared LED
- Peak wavelength typ. 850nm
- Half angle SFH 4258: $\pm 15^\circ$
- Half angle SFH 4259: $\pm 25^\circ$
- High forward current allowed at high temperature

Applications

- Infrared Illumination for CMOS cameras
- IR Data Transmission
- optical sensors

Safety Advices

Depending on the mode of operation, these devices emit highly concentrated non visible infrared light which can be hazardous to the human eye. Products which incorporate these devices have to follow the safety precautions given in IEC 60825-1 "Safety of laser products".

Type Type	Bestellnummer Ordering Code	Strahlstärkegruppierung¹⁾ ($I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$) Radiant Intensity Grouping¹⁾ $I_e \text{ (mW/sr)}$
SFH 4258	Q65110A2975	≥ 40 (typ. 90)
SFH 4259	Q65110A2464	≥ 25 (typ. 55)

¹⁾ gemessen bei einem Raumwinkel $\Omega = 0.01 \text{ sr}$ / measured at a solid angle of $\Omega = 0.01 \text{ sr}$



ATTENTION - Observe Precautions For Handling - Electrostatic Sensitive Device

Grenzwerte
Maximum Ratings

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebstemperatur Operating temperature range	T_{op}	- 40 ...+ 100	°C
Lagertemperatur Storage temperature range	T_{stg}	- 40 ...+ 100	°C
Sperrspannung Reverse voltage	V_R	3	V
Vorwärtsstrom, $T_A \leq 65$ °C Forward current	I_F	100	mA
Stoßstrom, $t_p = 10$ µs, $D = 0$, $T_A = 25$ °C Surge current	I_{FSM}	1.5	A
Verlustleistung $T_A = 25$ °C Power dissipation	P_{tot}	180	mW
Wärmewiderstand Thermal resistance			
Sperrschicht/Umgebung Junction/ambient	R_{thJA}	300	K/W
Sperrschicht/Lötpad Junction/soldering point	R_{thJS}	140	K/W
Montage auf PC-Board FR 4 (Padgröße ≥ 16 mm ²) mounted on PC board FR 4 (pad size ≥ 16 mm ²)			

Kennwerte ($T_A = 25$ °C)
Characteristics

Bezeichnung Parameter	Typ	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der Strahlung Wavelength at peak emission $I_F = 100$ mA		λ_{peak}	850	nm
Spektrale Bandbreite bei 50% von I_{max} Spectral bandwidth at 50% of I_{max} $I_F = 100$ mA		$\Delta\lambda$	35	nm
Abstrahlwinkel Half angle	SFH 4258 SFH 4259	φ	± 15 ± 25	Grad deg.
Aktive Chipfläche Active chip area		A	0.09	mm ²

Kennwerte ($T_A = 25\text{ °C}$)**Characteristics** (cont'd)

Bezeichnung Parameter	Typ	Symbol Symbol	Wert Value	Einheit Unit
Abmessungen der aktiven Chipfläche Dimension of the active chip area		$L \times B$ $L \times W$	0.3×0.3	mm
Schaltzeiten, I_e von 10% auf 90% und von 90% auf 10%, bei $I_F = 100\text{ mA}$, $R_L = 50\ \Omega$ Switching times, I_e from 10% to 90% and from 90% to 10%, $I_F = 100\text{ mA}$, $R_L = 50\ \Omega$		t_r, t_f	12	ns
Durchlassspannung Forward voltage $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$ $I_F = 1\text{ A}$, $t_p = 100\ \mu\text{s}$		V_F V_F	1.5 (< 1.8) 2.4 (< 3.0)	V V
Sperrstrom Reverse current $V_R = 3\text{ V}$		I_R	0.01 (≤ 10)	μA
Gesamtstrahlungsfluss Total radiant flux $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$		Φ_e	45	mW
Temperaturkoeffizient von I_e bzw. Φ_e , $I_F = 100\text{ mA}$ Temperature coefficient of I_e or Φ_e , $I_F = 100\text{ mA}$		TC_I	- 0.5	%/K
Temperaturkoeffizient von V_F , $I_F = 100\text{ mA}$ Temperature coefficient of V_F , $I_F = 100\text{ mA}$		TC_V	- 0.7	mV/K
Temperaturkoeffizient von λ , $I_F = 100\text{ mA}$ Temperature coefficient of λ , $I_F = 100\text{ mA}$		TC_λ	+ 0.2	nm/K

Strahlstärke I_e in Achsrichtung¹⁾

gemessen bei einem Raumwinkel $\Omega = 0.01$ sr

Radiant Intensity I_e in Axial Direction

at a solid angle of $\Omega = 0.01$ sr

Bezeichnung Parameter	Symbol	Werte Values			Einheit Unit
		SFH 4258-U	SFH 4258-V	SFH 4258-AW	
Strahlstärke Radiant intensity $I_F = 100$ mA, $t_p = 20$ ms	$I_{e \text{ min}}$	40	63	100	mW/sr
	$I_{e \text{ max}}$	80	125	200	mW/sr
Strahlstärke Radiant intensity $I_F = 1$ A, $t_p = 100$ μ s	$I_{e \text{ typ.}}$	400	600	800	mW/sr
		SFH 4259-T	SFH 4259-U		
Strahlstärke Radiant intensity $I_F = 100$ mA, $t_p = 20$ ms	$I_{e \text{ min}}$	25	40		mW/sr
	$I_{e \text{ max}}$	50	80		mW/sr
Strahlstärke Radiant intensity $I_F = 1$ A, $t_p = 100$ μ s	$I_{e \text{ typ.}}$	250	350		mW/sr

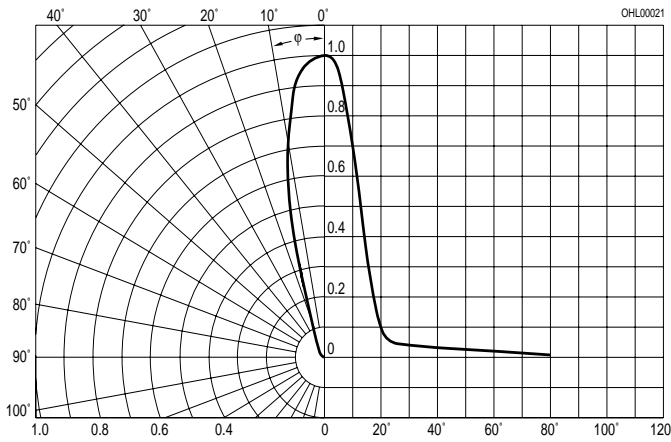
¹⁾ Nur eine Gruppe in einer Verpackungseinheit (Streuung kleiner 2:1)

¹⁾ Only one group in one packing unit, (variation lower 2:1)

Radiation Characteristics

$I_{rel} = f(\varphi)$

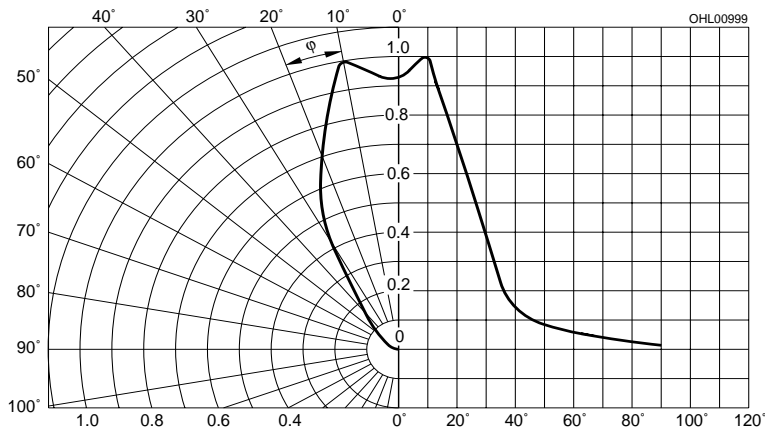
SFH 4258



Radiation Characteristics

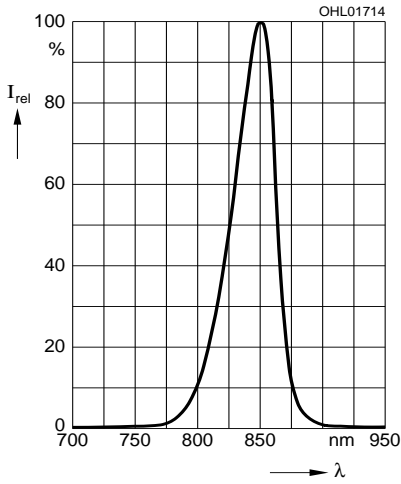
$I_{rel} = f(\varphi)$

SFH 4259



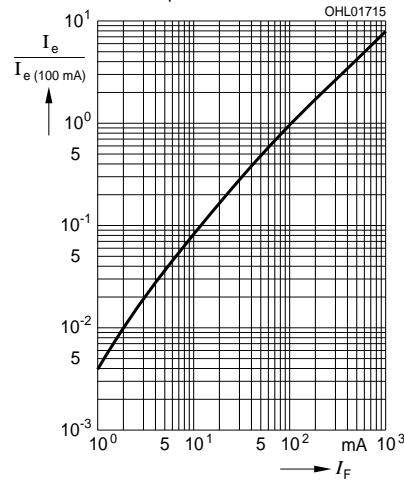
Relative Spectral Emission

$I_{rel} = f(\lambda)$



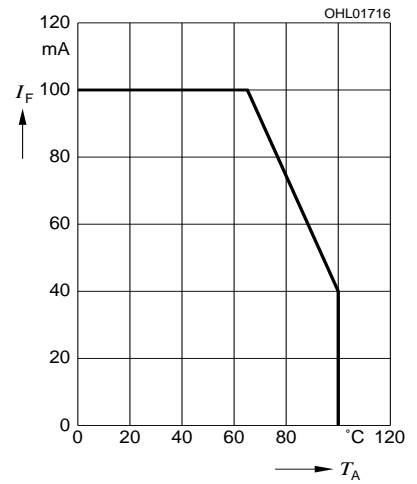
Radiant Intensity $\frac{I_e}{I_e(100 \text{ mA})} = f(I_F)$

Single pulse, $t_p = 20 \mu\text{s}$



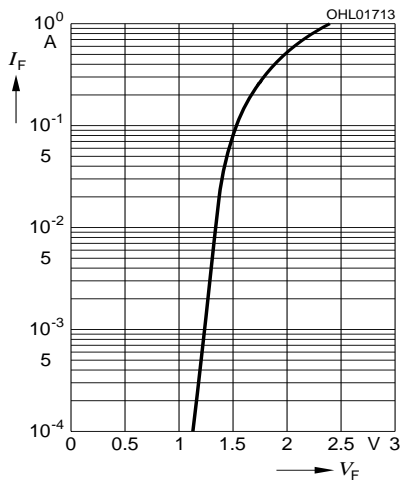
Max. Permissible Forward Current

$I_F = f(T_A), R_{thJA} = 300 \text{ K/W}^{(1)}$



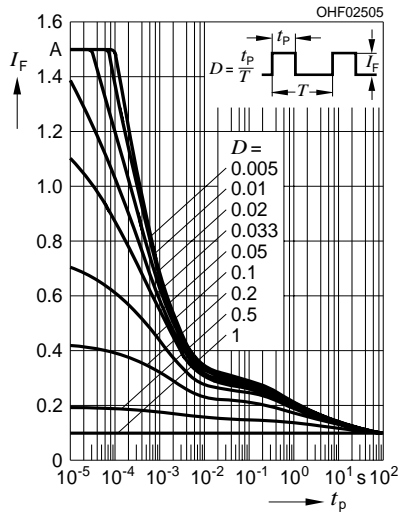
Forward Current $I_F = f(V_F)$

Single pulse, $t_p = 20 \mu\text{s}$



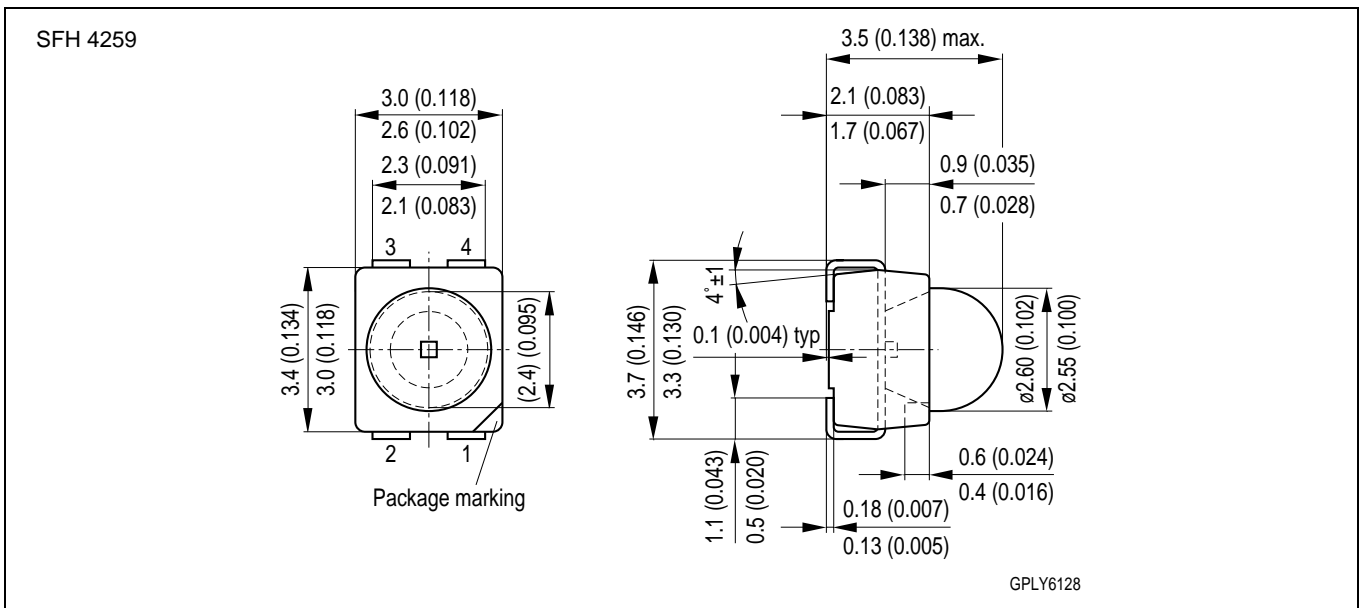
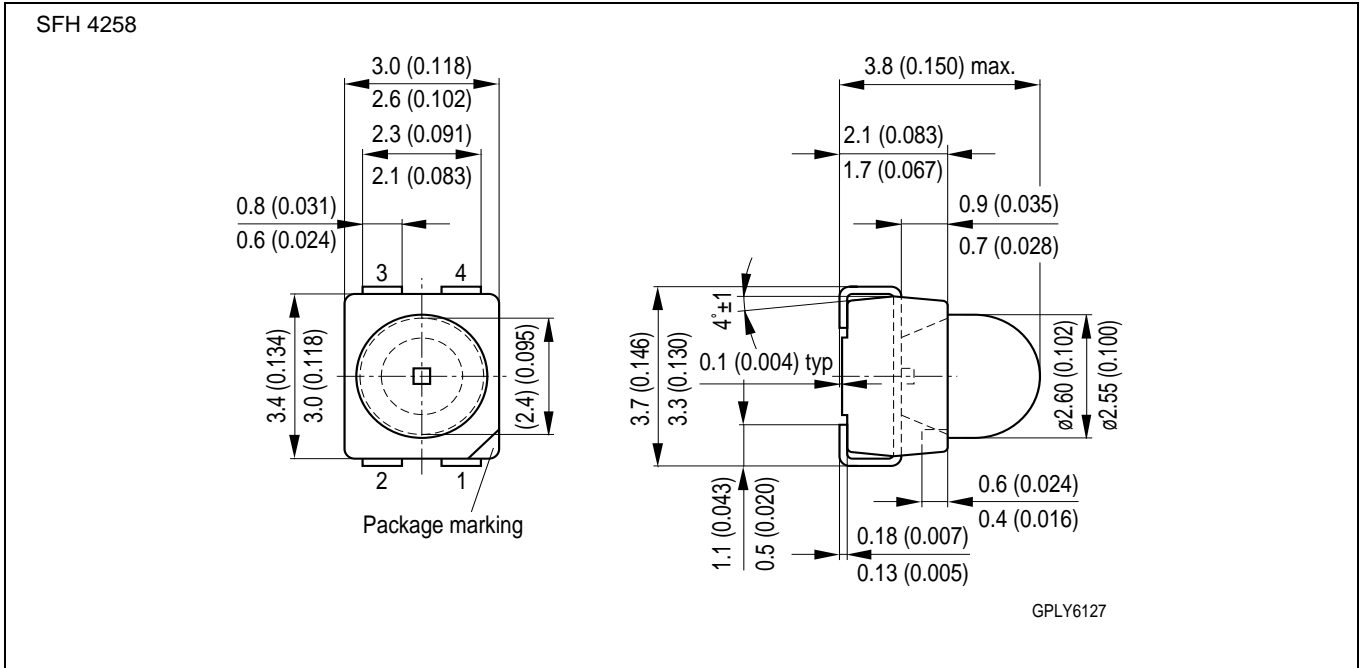
Permissible Pulse Handling Capability

$I_F = f(\tau), T_A = 25^\circ\text{C}$,
duty cycle $D = \text{parameter}^{(1)}$



¹⁾mounted on PC board FR 4
(pad size $\geq 16 \text{ mm}^2$)

Maßzeichnung
Package Outlines

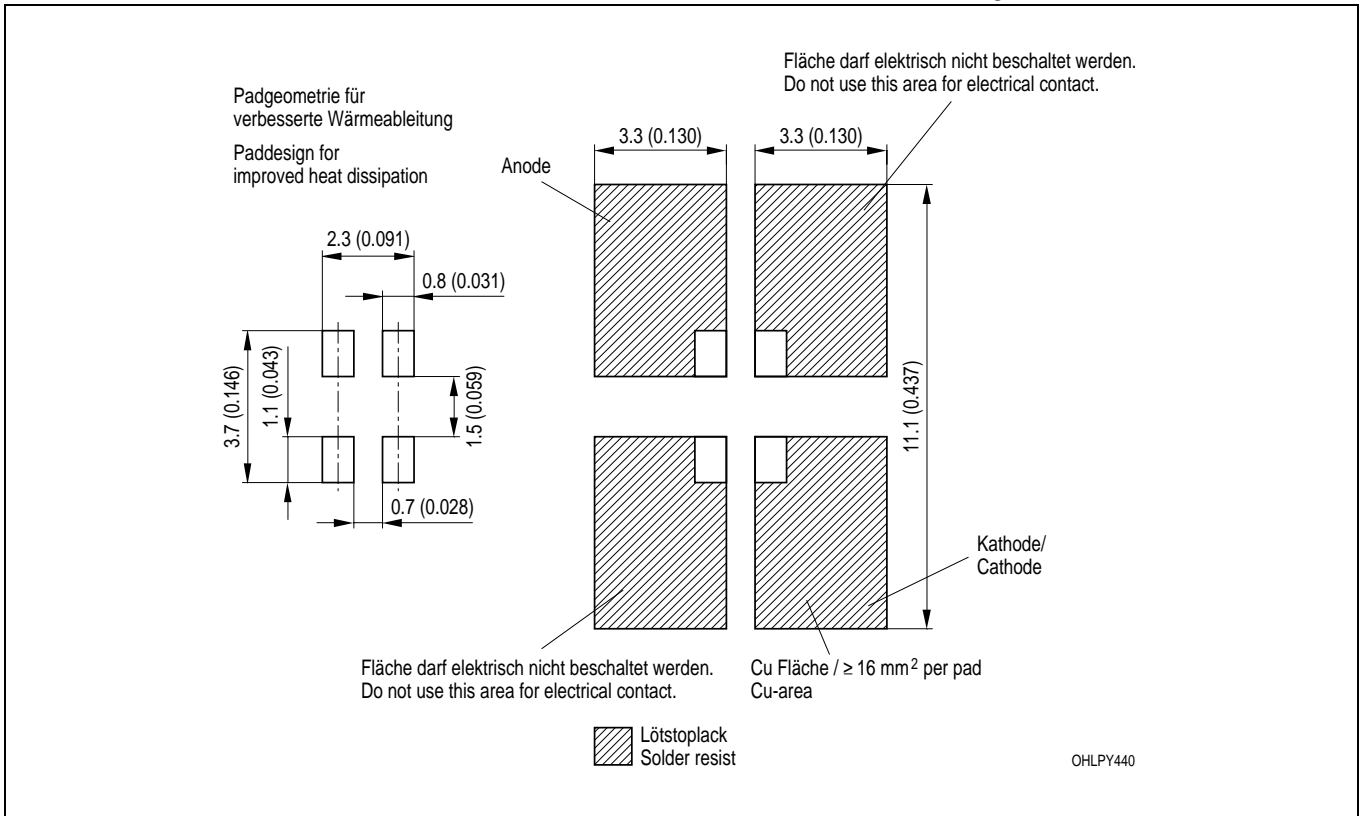


Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

Gehäuse / Package	Topled mit Linse, klares Gehäuse / Topled with lens, clear resin
Anschlussbelegung pin configuration	1 = Kathode / cathode 2/3/4 = Anode / anode

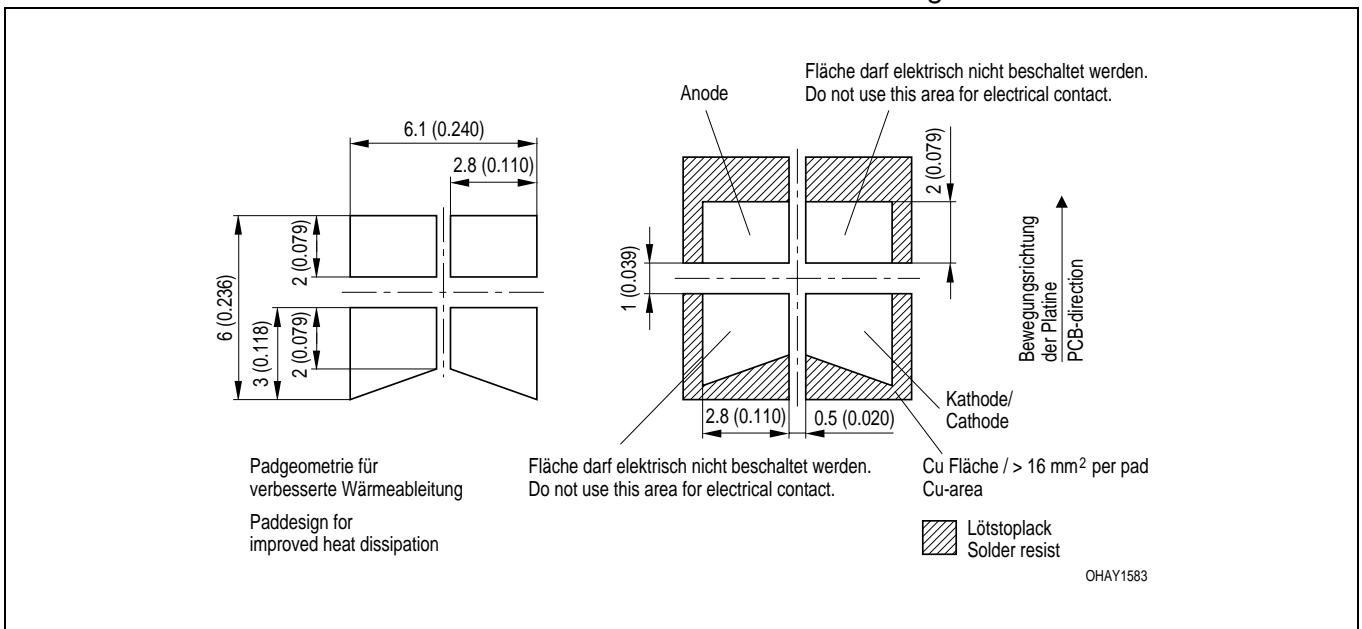
Empfohlenes Lötpad Design
Recommended Solder Pad

IR Flow Löten
IR Reflow Soldering



Empfohlenes Lötpad Design
Recommended Solder Pad

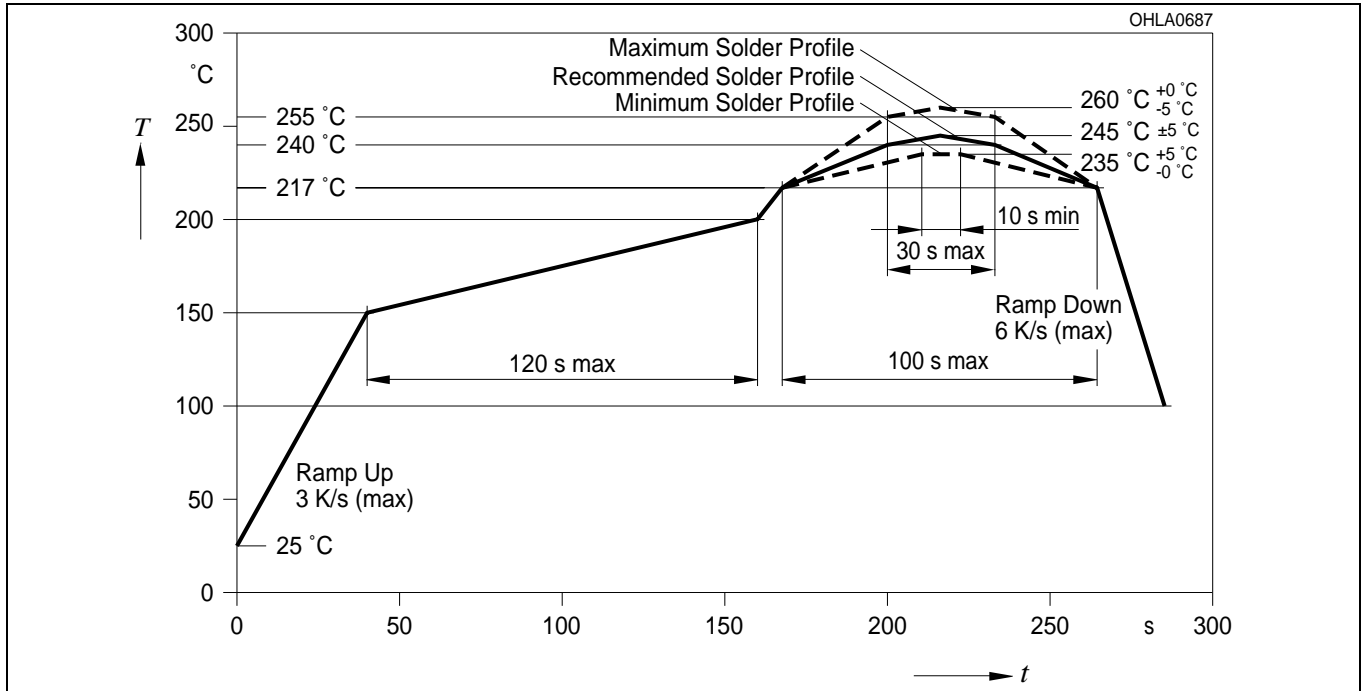
Wellenlöten TTW
TTW Soldering



Lötbedingungen
Soldering Conditions

IR-Reflow Lötprofil für bleifreies Löt
IR Reflow Soldering Profile for lead free soldering

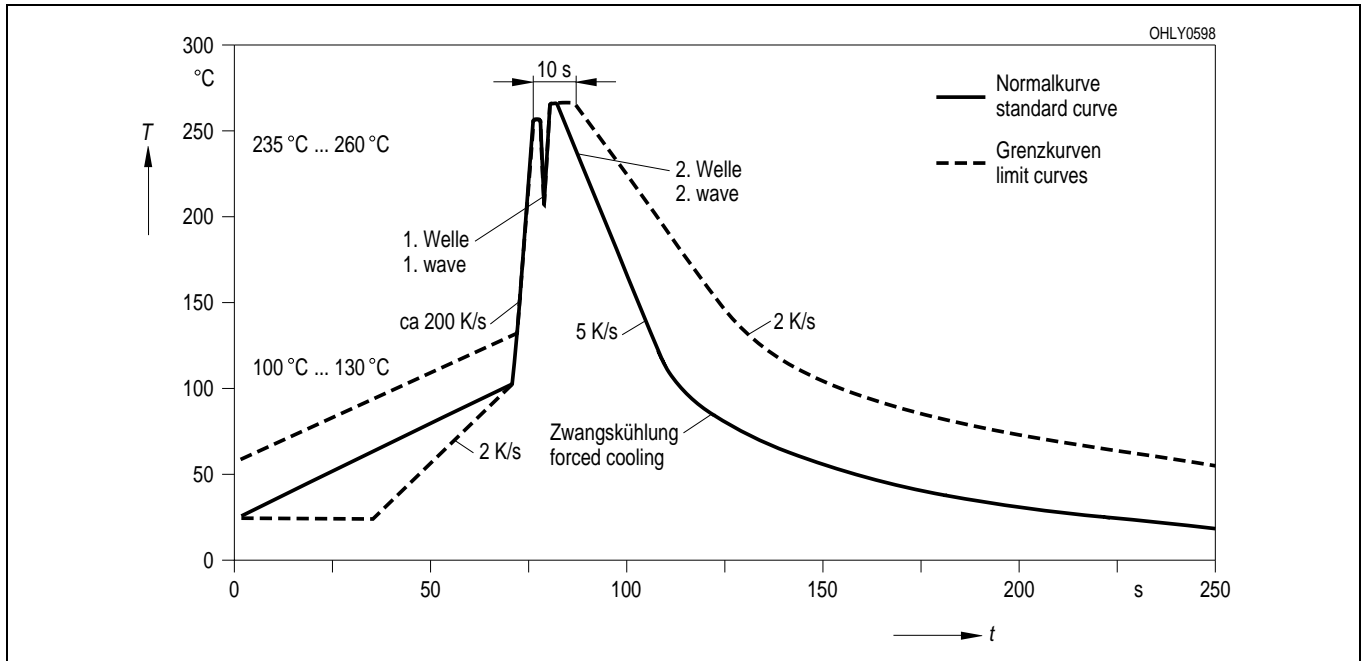
Vorbehandlung nach JEDEC Level 2
Preconditioning acc. to JEDEC Level 2
(nach J-STD-020B)
(acc. to J-STD-020B)



Lötbedingungen
Soldering Conditions

Wellenlöten (TTW)
TTW Soldering

Vorbehandlung nach JEDEC Level 2
Preconditioning acc. to JEDEC Level 2
(nach CECC 00802)
(acc. to CECC 00802)



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